2SC4003

Rev.E May.-2016

DATA SHEET

/ Descriptions

TO-252	NPN	Silicon NPN transistor in a TO-252 Plastic Package.

/ Features

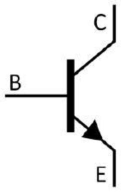
MBIT

High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity.

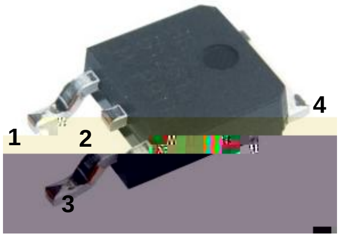
/ Applications

High voltage driver applications.

/ Equivalent Circuit



/ Pinning



PIN1	Base
PIN 2,4	Collector
PIN 3	Emitter

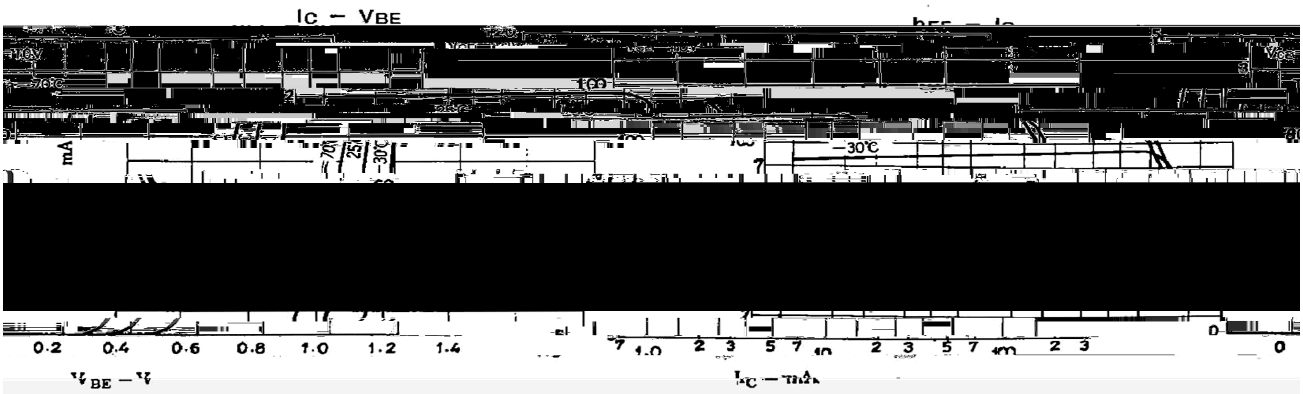
/ h_{FE} Classifications & Marking

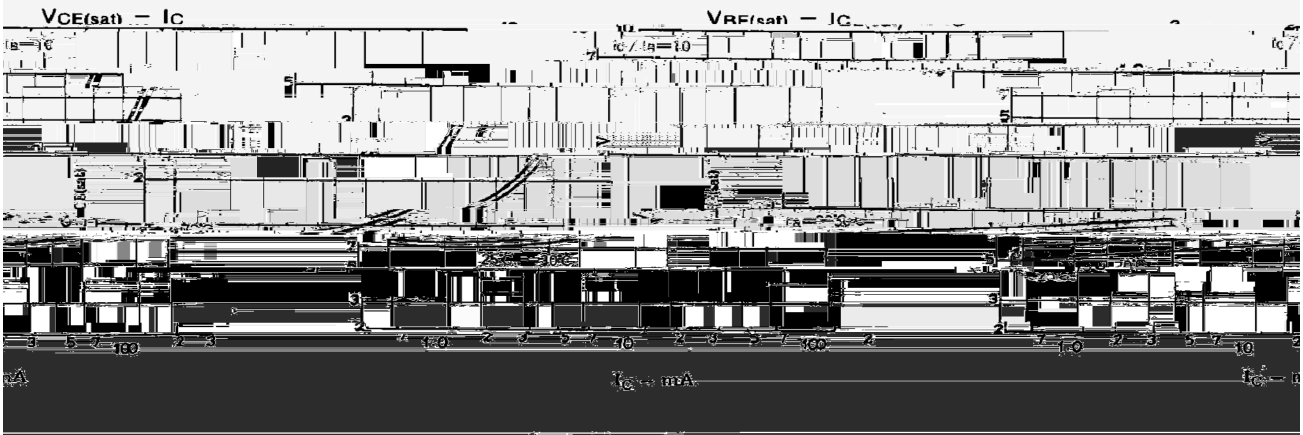
h_{FE} Classifications Symbol	D	E
h_{FE} Range	60 120	100 200

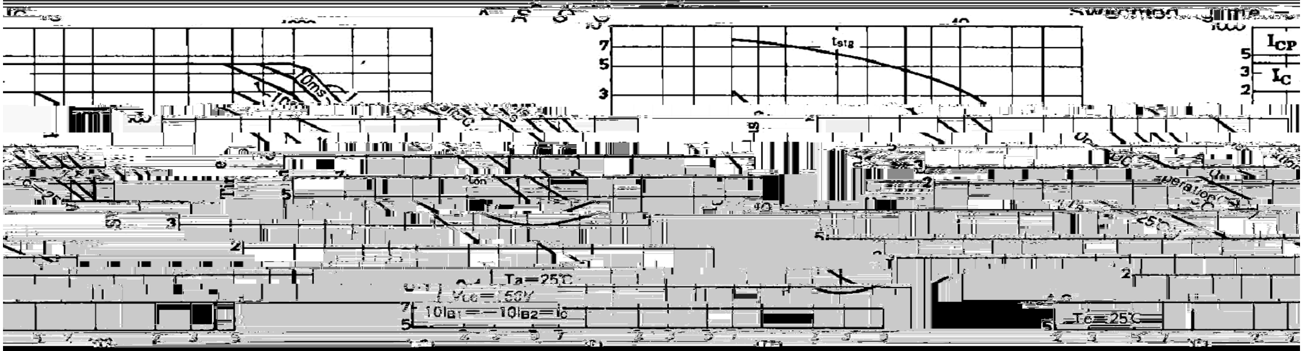
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	400	V
Collector to Emitter Voltage	V_{CEO}	400	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	200	mA
Collector Current – Continuous(Pulse)	I_{CP}	400	mA
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	P_C(T_c=25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

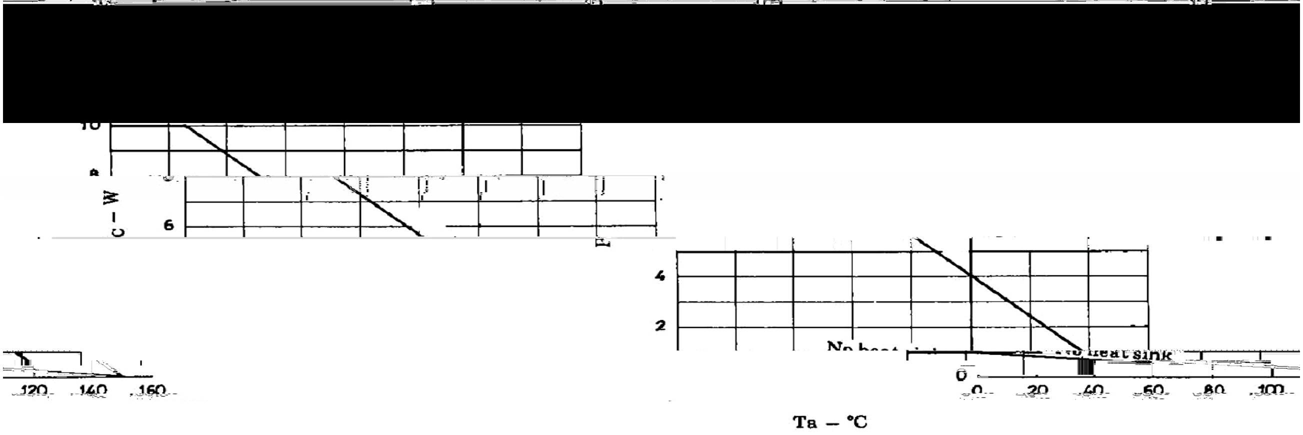
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10μA I_E=0	400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA R_{BE}=∞				

/ Electrical Characteristic Curve

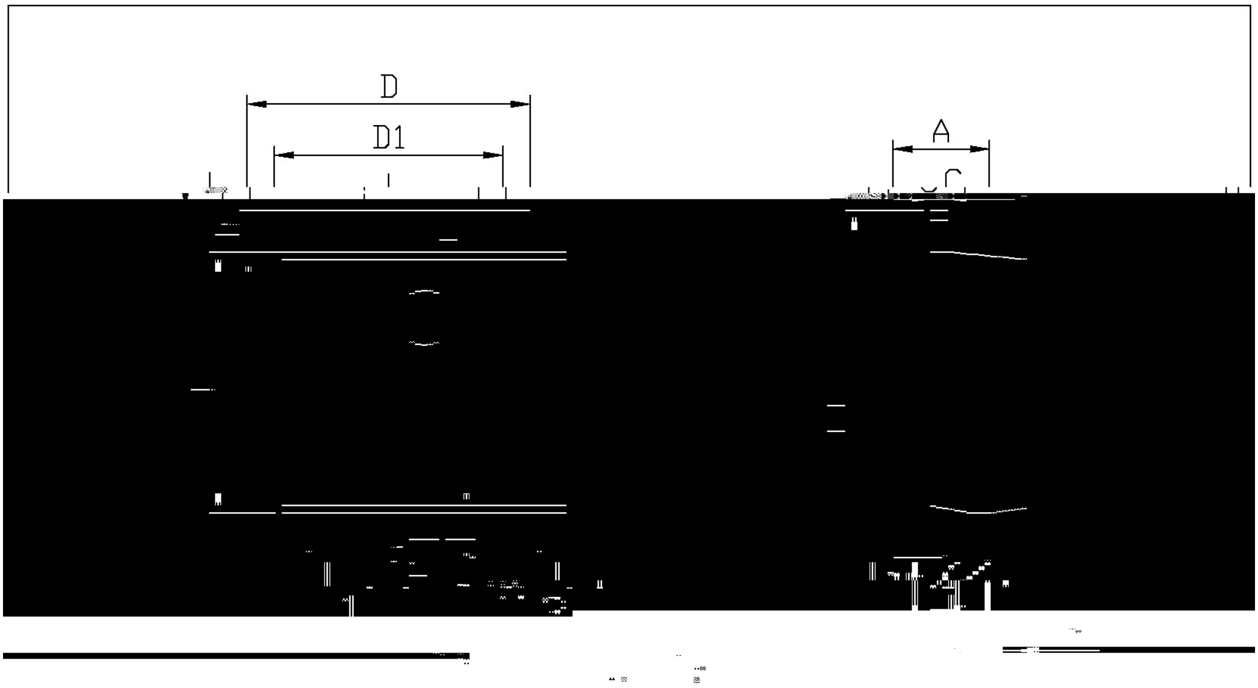








/ Package Dimensions

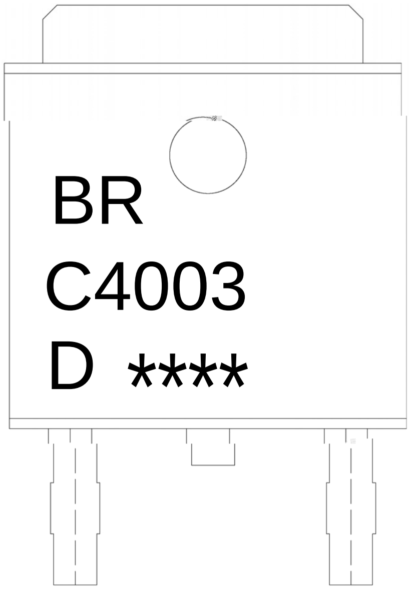


0.60	0.90
0.00	0.10

D	6.45	6.75	L3	
D1	5.10	5.50	K	

TO-252

/ Marking Instructions



BR

C4003

D: h_{FE}

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Note:

BR: Company Code

C4003: Product Type.

D: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.